

CentralTM Semiconductor Corp.

145 Adams Ave., Hauppauge, NY 11788 USA
Phone (516) 435-1110 FAX (516) 435-1824

Manufacturers of World Class Discrete Semiconductors

CMPFJ310

SURFACE MOUNT
SILICON N-CHANNEL JFET

SOT-23 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR CMPFJ310 type is a epoxy molded N-Channel Silicon Junction Field Effect Transistor manufactured in an SOT-23 case, designed for VHF/UHF amplifier applications.

Marking code is 6T.

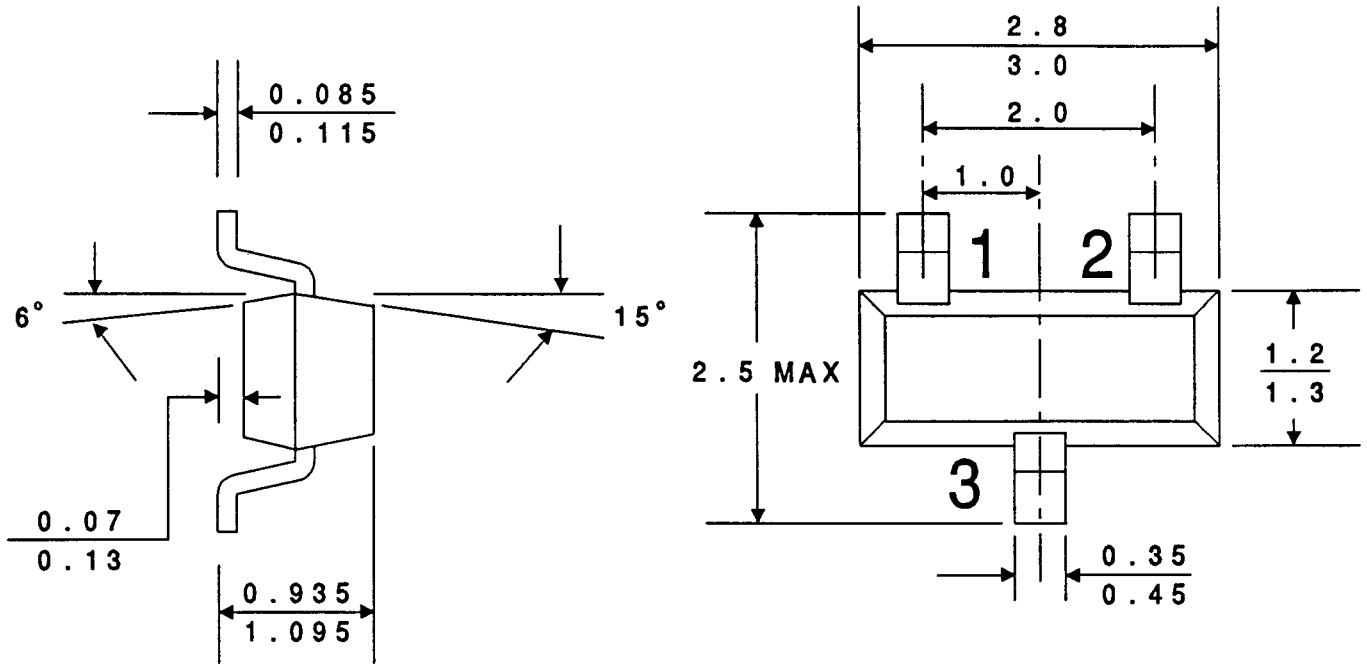
MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

	<u>SYMBOL</u>		<u>UNITS</u>
Drain-Source Voltage	V_{DS}	25	V
Gate-Source Voltage	V_{GS}	25	V
Gate Current	I_G	10	mA
Power Dissipation	P_D	350	mW
Operating and Storage			
Junction Temperature	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
Thermal Resistance	θ_{JA}	357	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

<u>SYMBOL</u>	<u>TEST CONDITIONS</u>	<u>MIN</u>	<u>TYP</u>	<u>MAX</u>	<u>UNITS</u>
I_{GSS}	$V_{GS} = 15\text{V}$			1.0	nA
I_{GSS}	$V_{GS} = 15\text{V}, T_A = 125^\circ\text{C}$			1.0	μA
I_{DSS}	$V_{DS} = 10\text{V}, V_{GS} = 0$	24		60	mA
BV_{GSS}	$I_G = 1.0\mu\text{A}$	25			V
$V_{GS(off)}$	$V_{DS} = 10\text{V}, I_D = 1.0\text{nA}$	2.0		6.5	V
$V_{GS(f)}$	$I_G = 1.0\text{mA}, V_{DS} = 0$			1.0	V
$ Y_{fs} $	$V_{DS} = 10\text{V}, I_D = 10\text{mA}, f = 1.0\text{kHz}$	8.0		18	mmhos
$ Y_{os} $	$V_{DS} = 10\text{V}, I_D = 10\text{mA}, f = 1.0\text{kHz}$			250	μmhos
C_{iss}	$V_{GS} = 10\text{V}, V_{DS} = 0, f = 1.0\text{MHz}$			5.0	pF
C_{rss}	$V_{GS} = 10\text{V}, V_{DS} = 0, f = 1.0\text{MHz}$			2.5	pF
\bar{e}_n	$V_{DS} = 10\text{V}, I_D = 10\text{mA}, f = 100\text{Hz}$		10		$\text{nV}/\sqrt{\text{Hz}}$

All Dimensions in mm.



LEAD CODE:

MARKING CODE: 6T

- 1) SOURCE
- 2) DRAIN
- 3) GATE